

FAST RECOVERY DIODE

ARF695

FOR IGBT, IEGT, GCT APPLICATIONS

SNUBBERLESS OPERATION

LOW LOSSES SOFT RECOVERY

Repetitive voltage up to

6000 V

Mean forward current

901 A

Surge current

18 kA

FINAL SPECIFICATION

July 13 - Issue: 0

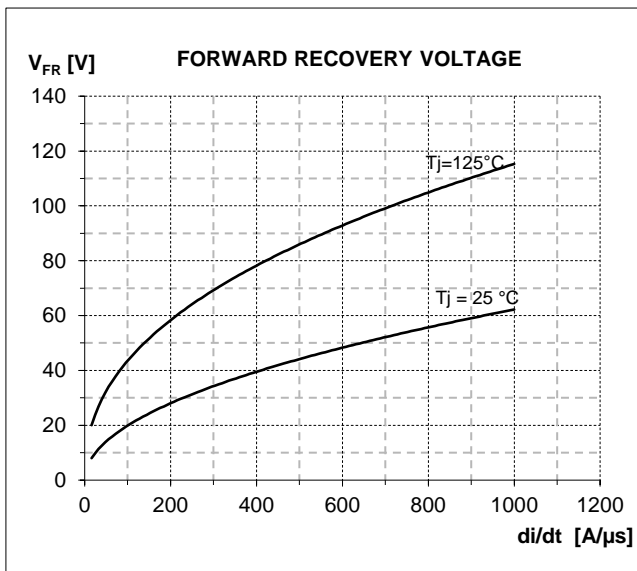
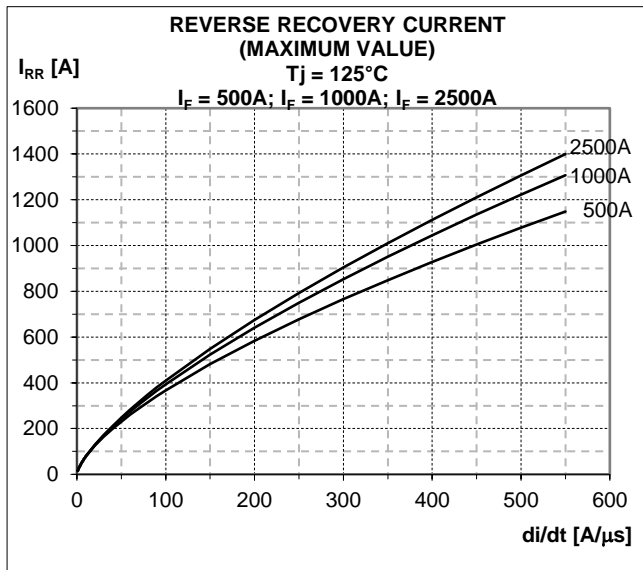
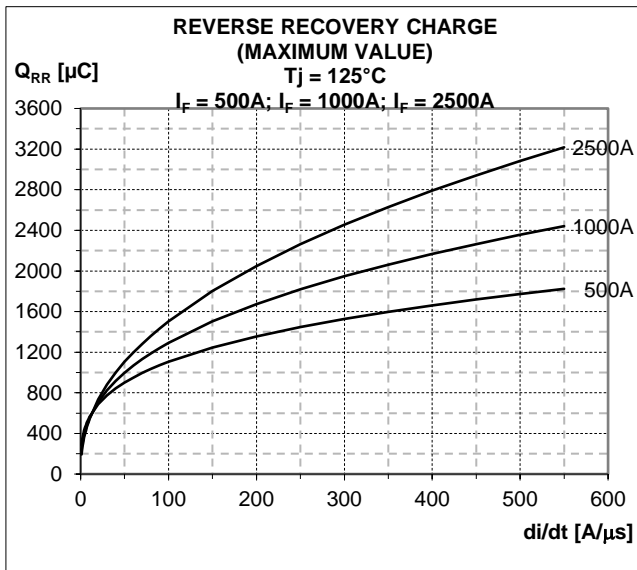
Symbol	Characteristic	Conditions	T _j [°C]	Value	Unit
BLOCKING					
V _{RRM}	Repetitive peak reverse voltage		125	6000	V
V _{RSM}	Non-repetitive peak reverse voltage		125	6100	V
I _{RRM}	Repetitive peak reverse current	V=V _{RRM}	125	75	mA
V _{DC LINK}	Permanent DC voltage		125	3200	V
CONDUCTING					
I _{F(AV)}	Mean forward current	180° sin, 50 Hz, Th=55°C, double side cooled		901	A
I _{F(AV)}	Mean forward current	180° sin, 50 Hz, Tc=85°C, double side cooled		738	A
I _{FSM}	Surge forward current	Sine wave, 10 ms	125	18	kA
I ² t	I ² t	with reverse voltage up to 50% VRSM		1620 x 10 ³	A ² s
V _{FM}	Forward voltage	Forward current = 1570 A	125	4,53	V
V _{F(TO)}	Threshold voltage		125	2,10	V
r _F	Forward slope resistance		125	1,550	mohm
SWITCHING					
Q _{RR}	Reverse recovery charge	IF= 1000 A VR= 100 V	125	1800	μC
I _{RR}	Peak reverse recovery current	di/dt= 250 A/μs Chord= 25 %		750	A
t _{RR}	Reverse recovery time	IF= 1000 A VR= 350 V		5	μs
Q _{RR}	Reverse recovery charge	di/dt= 500 A/μs Chord= 25 %	125	3000	μC
I _{RR}	Peak reverse recovery current			1300	A
S	Softness (s-factor), min			≥ 0,6	
E _{OFF}	Turn off energy dissipation			1	J
V _{FR}	Peak forward recovery	di/dt= 500 A/μs	125	≤ 130	V
MOUNTING					
R _{th(j-h)}	Thermal impedance, DC	Junction to heatsink, double side cooled		14,0	°C/kW
R _{th(c-h)}	Thermal impedance	Case to heatsink, double side cooled		3,0	°C/kW
T _j	Operating junction temperature			-30 / 125	°C
F	Mounting force			35 / 40	kN
	Mass			850	g

ORDERING INFORMATION : ARF695 S 60

standard specification

VRRM/100

SWITCHING CHARACTERISTICS



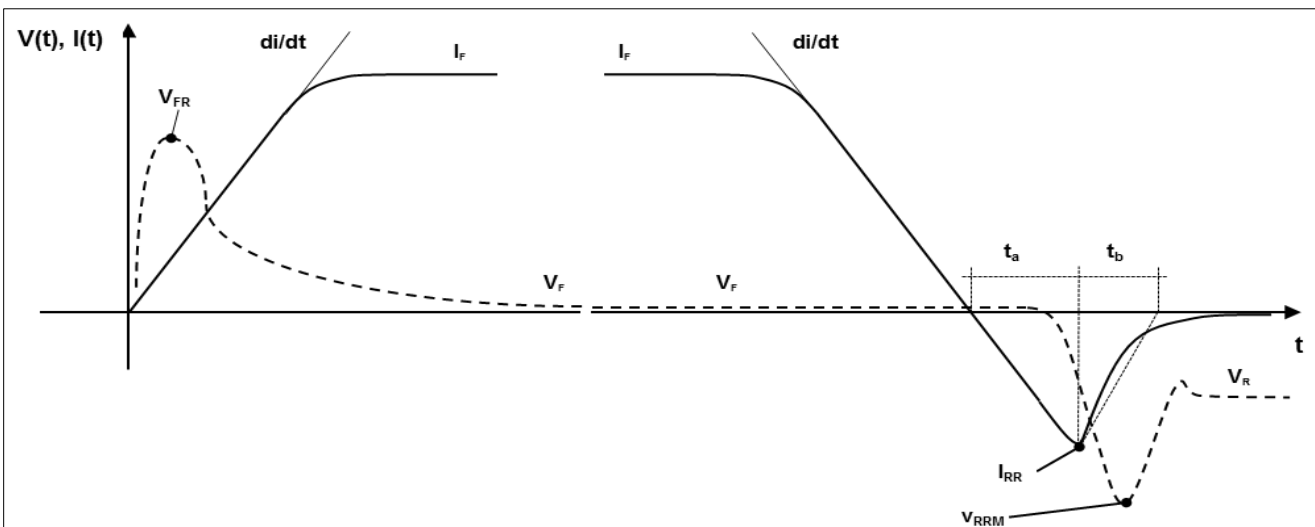
$$t_a = \frac{I_{RR}}{di/dt}$$

$$t_b = t_{RR} - t_a$$

$$S = \frac{t_b}{t_a}$$

$$E_{OFF} = V_R * \left[Q_{RR} - \left(I_{RR} * \frac{t_a}{2} \right) \right]$$

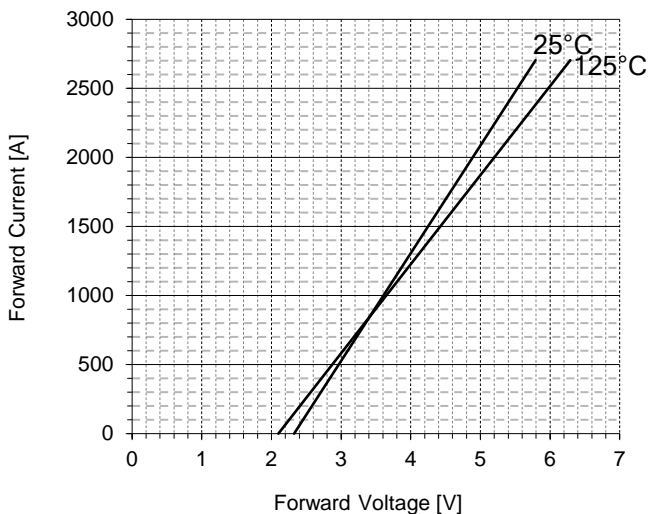
$$Q_{RR} = I_{RR} * \frac{t_{RR}}{2}$$



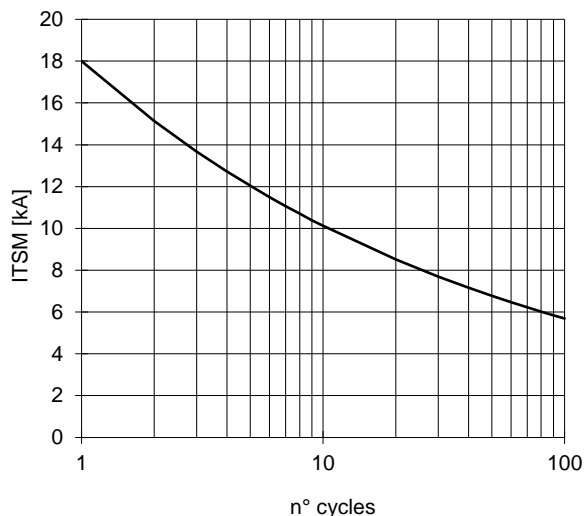
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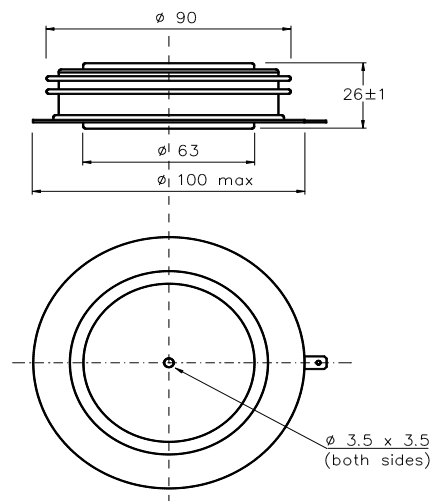
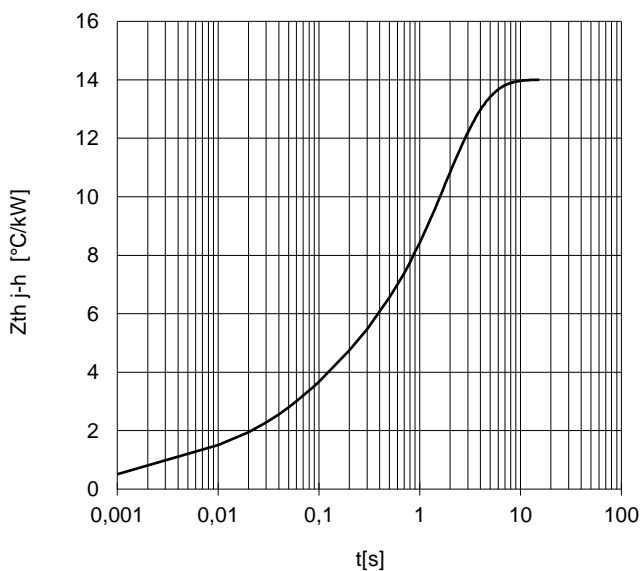
FORWARD CHARACTERISTIC
T_j = 125 °C
T_j = 25 °C



SURGE CHARACTERISTIC
T_j = 125 °C



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED



Dimensions
in mm



All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 μm.
In the interest of product improvement POSEICO SpA reserves the right to change any data given in this data sheet at any time without previous notice.
If not stated otherwise the maximum value of ratings (symbols over shaded background) and characteristics is reported.

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